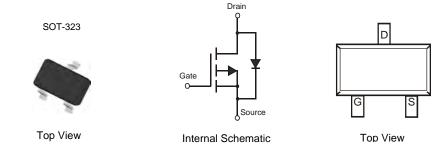


### **Features**

- P-Channel MOSFET
- Low On-Resistance
  - 150 mΩ @ V<sub>GS</sub> = -4.5V
  - 200 m $\Omega$  @ V<sub>GS</sub> = -2.5V
  - 240 m $\Omega$  @ V<sub>GS</sub> = -1.8V
- Very Low Gate Threshold Voltage V<sub>GS(th)</sub> ≤ 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

## **Mechanical Data**

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



#### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Chara	cteristic	Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Drain Current (Note 1)	T <sub>A</sub> = 25°C T <sub>A</sub> = 70°C	ID	-1.5 -1.0	A
Pulsed Drain Current		I <sub>DM</sub>	-5	A

## **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	PD	250	mW
Thermal Resistance, Junction to Ambient	$R_{ heta}$ JA	500	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes: 1. Device mounted on FR-4 substrate PC board, 2oz. Copper, with minimum recommended pad layout.

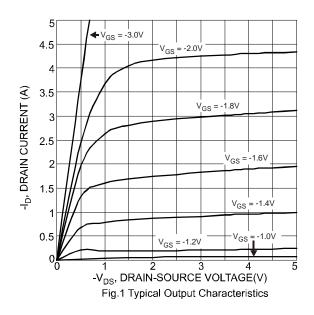
2. No purposefully added lead.

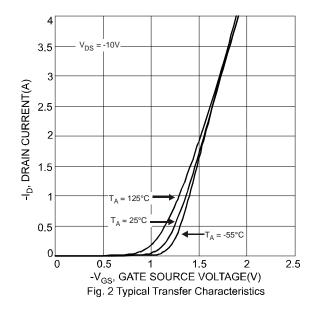
Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.



Electrical Characteristics @T <sub>A</sub> = 25°C unless otherwise specified						
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	—	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I <sub>DSS</sub>	_	_	-1.0 -5.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_		±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)	·					
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.45		-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		92 134 180	150 200 240	mΩ	$\label{eq:VGS} \begin{array}{l} V_{GS} = -4.5V, \ I_D = -2.0A \\ \hline V_{GS} = -2.5V, \ I_D = -1.5A \\ \hline V_{GS} = -1.8V, \ I_D = -0.5A \end{array}$
Forward Transconductance	<b>g</b> fs		3.1	—	S	$V_{DS} = -10V, I_{D} = -810mA$
Diode Forward Voltage (Note 4)	V <sub>SD</sub>	_	_	-0.9	V	$V_{GS} = 0V, I_{S} = -0.5A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	Ciss		320		pF	
Output Capacitance	Coss	—	80		pF	−V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V −f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>		60	—	pF	1 = 1.00012
Turn-On Delay Time	t <sub>D(on)</sub>		12.5	_	ns	
Turn-On Rise Time	tr	_	10.3	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(off)</sub>	_	46.5	_	ns	$R_L = 10\Omega, R_G = 1.0\Omega$
Turn-Off Fall Time	t <sub>f</sub>		22.2		ns	

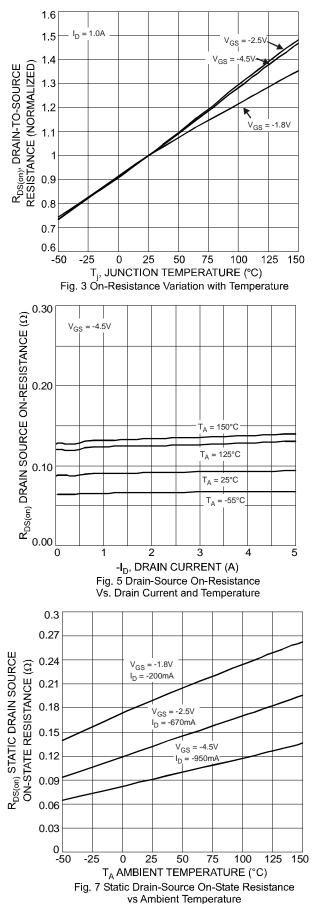
Notes: 4. Short duration pulse test used to minimize self-heating effect.

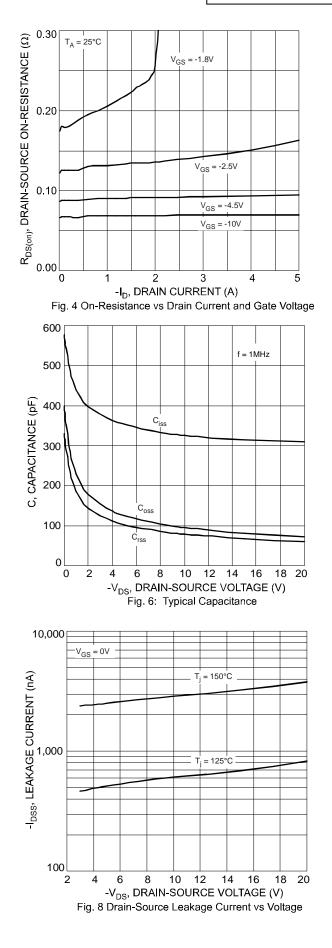




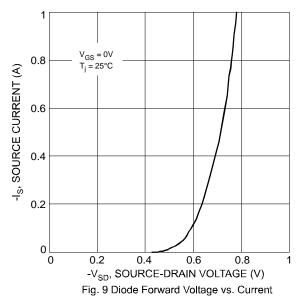
# **DMP2240UW**









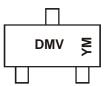


# Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2240UW-7	SOT-323	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

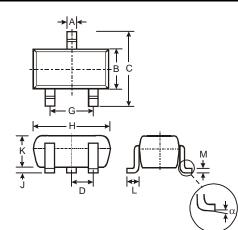
# **Marking Information**



DMV = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key												
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

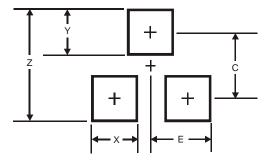
# **Package Outline Dimensions**



SOT-323					
Dim	Min	Max	Тур		
Α	0.25	0.40	0.30		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	-	-	0.65		
G	1.20	1.40	1.30		
н	1.80	2.20	2.15		
J	0.0	0.10	0.05		
К	0.90	1.00	1.00		
L	0.25	0.40	0.30		
М	0.10	0.18	0.11		
α	0°	8°	-		
All	All Dimensions in mm				



## **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

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  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
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